Pb Free Product



NCE P-Channel Enhancement Mode Power MOSFET

Description

The NCE30P30K uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge .This device is well suited for high current load applications.

General Features

V_{DS} =-30V,I_D =-30A

 $R_{DS(ON)}$ <18m Ω @ V_{GS} =-10V

 $R_{DS(ON)}$ <30m Ω @ V_{GS} =-4.5V

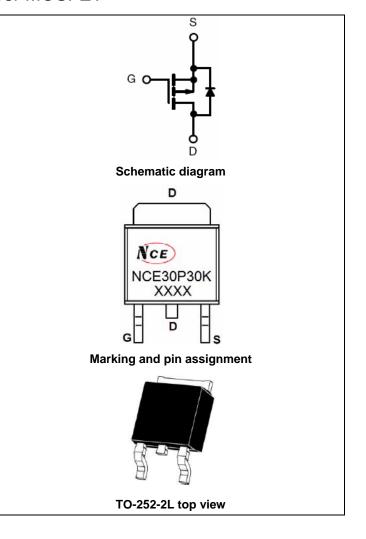
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

- High side switch for full bridge converter
- DC/DC converter for LCD display

100% UIS TESTED!

100% AVds TESTED!



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE30P30K	NCE30P30K	TO-252-2L	-	-	-

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	-30	V
Gate-Source Voltage	V _G S	±20	V
Drain Current-Continuous	I _D	-30	Α
Drain Current-Continuous(T _C =100 °C)	I _D (100℃)	-21.2	Α
Pulsed Drain Current	I _{DM}	-70	Α
Maximum Power Dissipation	P _D	60	W
Derating factor		0.4	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	169	mJ
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 175	$^{\circ}$



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NCE30P30K

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{eJC}	2.5	°C/W	Ī
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Electrical Characteristics (T_C=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics			•	•		
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA -30		-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V,V _{GS} =0V	-	-	-1	μΑ
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=-250\mu A$	-1.2	-1.6	-2.5	V
Drain-Source On-State Resistance	Б	V_{GS} =-10V, I_D =-20A	-	13	18	mΩ
Diditi-Source Oil-State Resistance	R _{DS(ON)}	V_{GS} =-4.5V, I_{D} =-15A	-	22	30	mΩ
Forward Transconductance	g FS	V _{DS} =-5V,I _D =-20A	-	25	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	\/ - 45\/\/ -0\/	-	1363	-	PF
Output Capacitance	C _{oss}	V_{DS} =-15V, V_{GS} =0V, F=1.0MHz	-	250	-	PF
Reverse Transfer Capacitance	C _{rss}	r-1.0ivinz	-	210	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	9	-	nS
Turn-on Rise Time	t _r	V_{DD} =-30V, R_L =3 Ω ,	-	10	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =-10 V , R_{G} =2.5 Ω	-	50	-	nS
Turn-Off Fall Time	t _f		-	20	-	nS
Total Gate Charge	Qg	\/ - 451 - 450	-	31.2		nC
Gate-Source Charge	Q _{gs}	V _{DS} =-15,I _D =-15A, V _{GS} =-10V	-	3.2		nC
Gate-Drain Charge	Q _{gd}	VGS=-10V	-	9.2		nC
Drain-Source Diode Characteristics	<u>.</u>		•	•		
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-15A	-		-1.2	V
Diode Forward Current (Note 2)	Is		-	-	-20	Α
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF =- 15A	-	24		nS
Reverse Recovery Charge	Qrr	$di/dt = -100A/\mu s^{(Note3)}$	_	16		nC

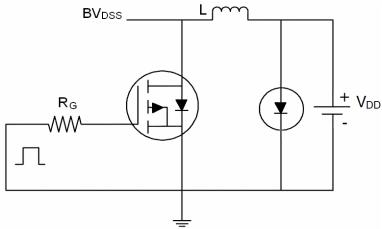
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- **5.** E_{AS} condition: $Tj=25^{\circ}C$, $V_{DD}=-15V$, $V_{G}=-10V$,L=0.5mH, $Rg=25\Omega$, $I_{AS}=-26A$

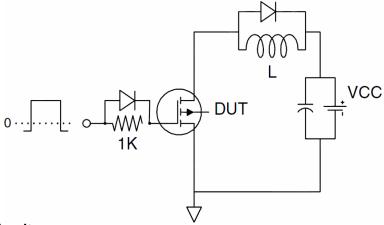


Test Circuit

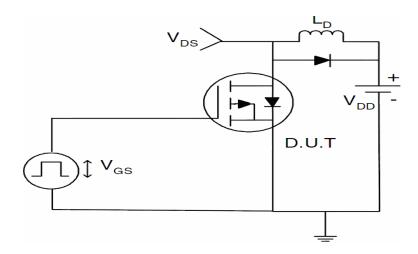
1) E_{AS} Test Circuit



2) Gate Charge Test Circuit

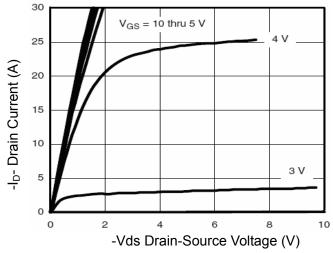


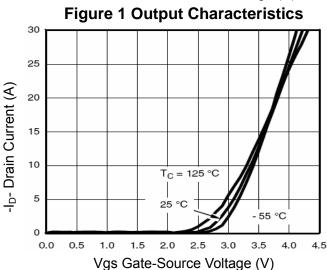
3) Switch Time Test Circuit

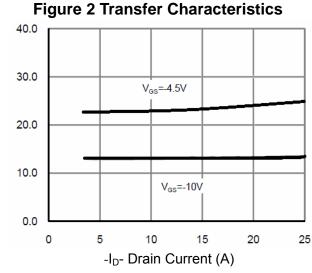












Rdson On-Resistance(m 2)

Figure 3 Rdson- Drain Current

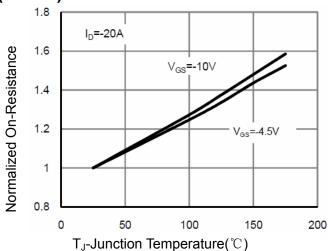
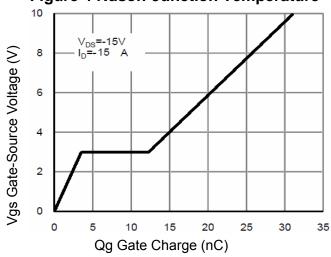


Figure 4 Rdson-Junction Temperature



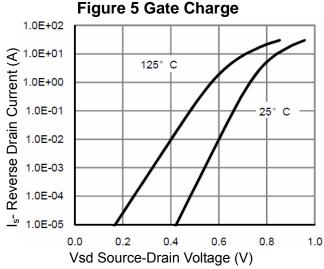
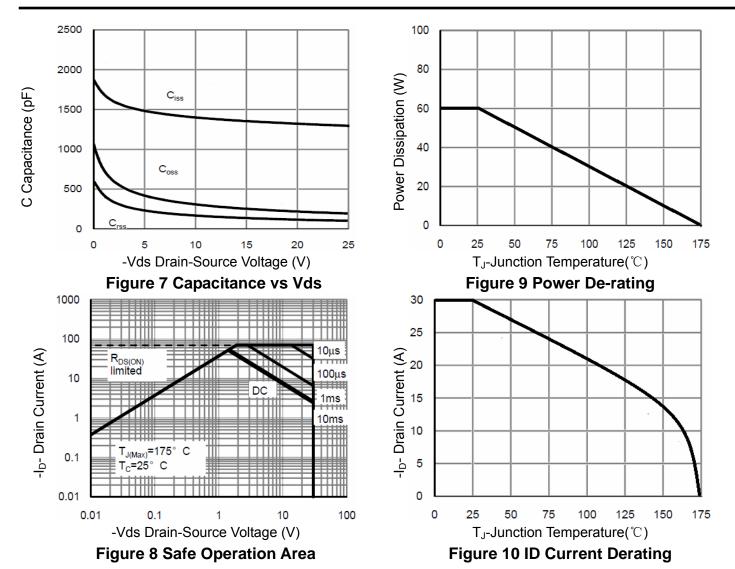


Figure 6 Source- Drain Diode Forward





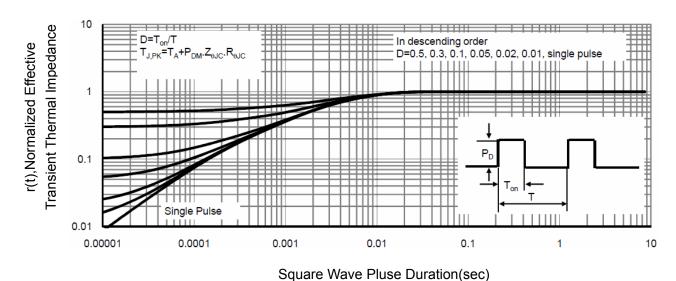
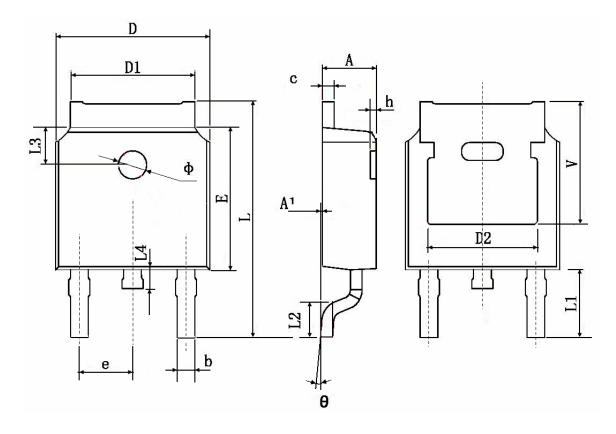


Figure 11 Normalized Maximum Transient Thermal Impedance

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TO-252 Package Information



Symbol	Dimensions I	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.830	TYP.	0.190 TYP.		
Е	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900	TYP.	0.114	0.114 TYP.	
L2	1.400	1.700	0.055	0.067	
L3	1.600	1.600 TYP. 0.063 TYP.		TYP.	
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350	TYP.	0.211 TYP.		



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NCE30P30K

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